

COMPUTER DIODE

Switching

1N3064
 1N4454
 1N4454-1

FEATURES

- Metallurgical Bond
- Planar Passivated Chip
 DO-35 Package

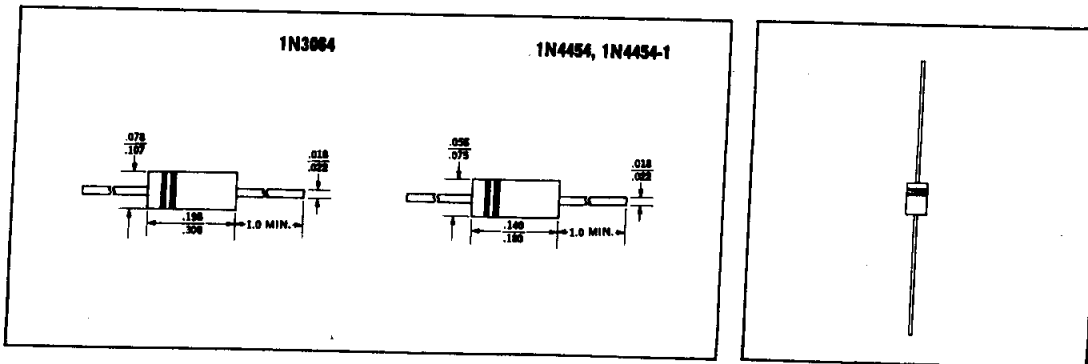
DESCRIPTION

Available in either DO-35 or DO-7 package.
 high temperature
 metallurgical bond, making these devices
 useful in high reliability applications.

ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage	75V
Peak Working Voltage	50V
Average Output Current, 1N3064	75mA
1N4454,-1	200mA
Surge Current, 1sec 1N3064	0.5A
1N4454,-1	1.0A
Operating Temperature Range	-65°C to +175°C
Storage Temperature Range	-65°C to +200°C

MECHANICAL SPECIFICATIONS



ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Type	Reverse Current @ 25°C	Reverse Current @ 150°C	Reverse Breakdown Voltage @ -65°C	Reverse Recovery Time	Capacitance
1N3064 1N4454 1N4454-1	0.1 μ Adc @ $V_R = 50V$	100 μ Adc @ $V_R = 50V$	75Vdc @ $I_R = 10\mu$ Adc	4nsec @ $I_F = I_R = 10mAdc$ $R_T = 100$ ohms $c \leq 3pf$	2.0pf @ $V_R = 0$ Vdc, $f = 1$ MHz $v_{sig} = 50mV$ (pk to pk)

Forward Voltage	Forward Recovery Voltage	Forward Recovery Time
1.0 Vdc @ $I_F = 10mAdc$	5.0V (pk) @ $I_F = 100mAdc$ $t_r \leq 0.4nsec$	30nsec $I_F = 100mAdc$ $t_r \leq 0.4nsec$

